

Room-temperature ferromagnetism of single-crystalline MoS₂ nanowires

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Single-crystalline molybdenum disulphide (MoS₂) nanowires are prepared by a hydrothermal method. The single-crystalline MoS₂ nanowires display substantial ferromagnetism at room temperature. The S vacancies and Mo-edges are possible mechanisms responsible for the observed ferromagnetism at room temperature.

1. Introduction: Solid molybdenum disulphide (MoS₂) has a distinct layered structure, in which each Mo layer is sandwiched between two sulphur layers [1–5]. Bulk MoS₂ has wide applications in the fields of solid lubricants [6–8], catalyst [9, 10] and energy storage [11]. Since the hexagonal layered structure of MoS₂ is similar to that of graphite [1], mechanical exfoliation has been successfully applied to isolate the monolayer MoS₂ [12–14]. The monolayer MoS₂ has also been grown on a Cu substrate [15]. The success in isolating the monolayer MoS₂ renders the fabrication of one-dimensional MoS₂ nanostructures such as MoS₂ nanoribbons and single-walled MoS₂ possible [14, 16–20]. Unlike graphene, which is a zero-gap semi-metal or bulk MoS₂ which is a semiconductor with an indirect gap, the monolayer MoS₂ has been shown by both experiments and first-principles calculations to be a semiconductor with a direct bandgap [12, 21–23]. The direct bandgap character opens the possibility for the application of the monolayer MoS₂ as transistors [14, 16, 17, 21, 24], light-emitting diodes and solar cells.

Bulk MoS₂ is known to be a non-magnetic material. Compared with bulk materials, low-dimensional nanostructured materials have special physical properties, which is because of their anisotropic property and a unique size effect. Recent studies on the magnetic response of MoS₂ are limited to theoretical calculations [25–28]. These calculations predicted ferromagnetism in MoS₂ in the presence of zigzag Mo-edges [25–27] and sulphur vacancies [28]. From this point of view, in the presence of zigzag edges, magnetism should be observed in MoS₂ nanoribbons, nanocrystalline thin films and even in bulk limit provided that the average grain size is small enough. Ferromagnetism was observed in MoS₂ thin film [29] and MoS₂ bulk [30] with small grain size at room temperature, which was attributed to the existence of the zigzag edges in the ferromagnetic ground state.

To the best of our knowledge, the magnetic properties of single-crystalline MoS₂ nanowires have not yet been reported. In this Letter, we report ferromagnetism of single-crystalline MoS₂ nanowires at room temperature.

2. Experimental

2.1. Synthesis of MoS₂ nanowires: MoS₂ nanowires were prepared by a hydrothermal process. All chemicals used in this work were of analytic purity. In a typical procedure, 2.5 mmol of Na₂MoO₄·2H₂O and 5 mmol of CH₄N₂S were dissolved in 35 ml of distilled water, and then 3.5 ml concentrated hydrochloric acid was added into the reaction solution under violent stirring. The resulting solution was transferred into a 50 ml Teflon-lined

stainless autoclave and tightly sealed, which was kept at 220°C for 36 h. Then the autoclave was allowed to cool to room temperature naturally. The resulting products were filtered off, washed with distilled water and absolute ethanol several times and dried in vacuum at 60°C for 12 h for characterisation.

2.2. Characterisation: The microstructure of MoS₂ nanowires was characterised at room temperature by X-ray diffraction (XRD, Shimadzu XRD-7000 X-ray diffractometer) with Cu K α radiation. The surface morphology of the MoS₂ nanowires was characterised using a scanning electron microscope (SEM, JSM-6510). The size and crystal structure of the MoS₂ nanowires were observed by transmission electron microscopy (JEM-2100). The magnetic properties were characterised by a vibrating sample magnetometer from the Microsense Corporation, USA.

3. Results and discussion: The powder XRD pattern of the samples is shown in Fig. 1a. It can be seen that the diffraction peaks are indexed as MoS₂. The peaks with *d* spacing of 6.4, 2.7, 1.6 and 1.2 Å correspond to the (002), (100), (103) and (110) reflections, respectively, of nanostructured 2H-MoS₂ (JCPDS 37–1492). Meanwhile, the peaks with *d* spacing of 3.2 and 2.7 Å are attributed to the (004), (101) reflections of nanostructured 3R-MoS₂ (JCPDS 17–0744). The energy dispersive X-ray (EDX) data in Fig. 1b confirms that the nanowire has only Mo and S without any other impurities. The Al peaks are because of the substrate used for dispersing the samples, which indicate we have not mixed any impurity element in the preparation process. In

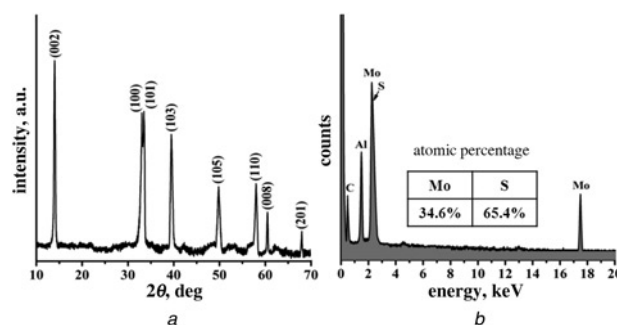


Figure 1 XRD pattern of MoS₂ nanowires (Fig. 1a), and EDX spectrum of MoS₂ nanowires (Fig. 1b), inset of Fig. 1b shows S/Mo atomic ratios obtained by EDX

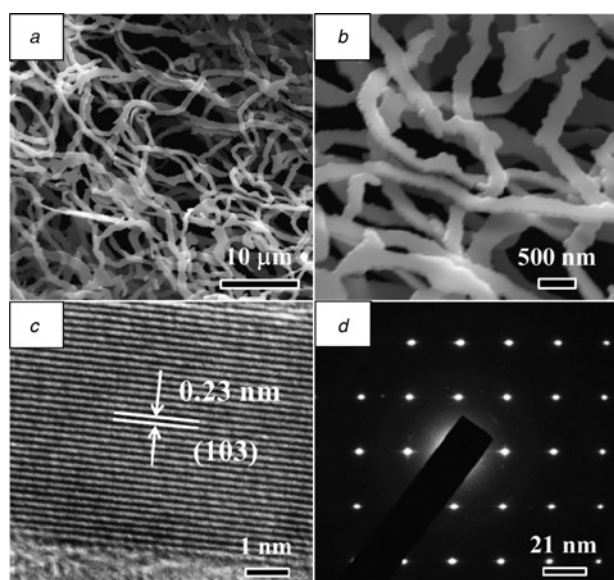


Figure 2 Low-magnification (Fig. 2a) and high-magnification (Fig. 2b) SEM image of MoS₂ nanowires; HRTEM image of individual MoS₂ nanowires (Fig. 2c); SAED pattern of MoS₂ nanowires (Fig. 2d)

addition, the inset to Fig. 1b shows S/Mo atomic ratios obtained by EDX. Since the S/Mo atomic ratios are 1.89, the nanowires are not completely sulphided, which is also observed in a previous report [30].

Figs. 2a and b show the SEM images of MoS₂ nanowires on adhesive tape. The size of the MoS₂ nanowires are about dozens of microns in length and 500 nm diameter. Fig. 2c is a high-resolution transmission electron microscope (HRTEM) image of the individual MoS₂ nanowires. The planes with interplanar spacing of 0.23 nm are corresponding to the (103) crystal faces. The corresponding selected area electron diffraction (SAED) pattern (Fig. 2d) indicates that the MoS₂ nanowires show an excellent single-crystalline structure.

The hysteresis loop (M–H) of MoS₂ nanowires with a magnetic field from –2 to 2 T at room temperature is shown in Fig. 3a. The single-crystalline MoS₂ nanowires show obvious ferromagnetism with coercivity about 200 Oe at room temperature (inset to Fig. 3a). The saturation magnetisation is about 1.1 emu/g. Fig. 3c shows that MoS₂ nanowires powder are strongly attracted by the permanent magnet. Therefore the MoS₂ nanowires show substantial ferromagnetism at room temperature. Ferromagnetism of the MoS₂ originating from the presence of zigzag Mo-edges and sulphur vacancies was predicted [25–28], where zigzag Mo-edges and sulphur vacancies can lead to strong ferromagnetism of several μ_B /atom.

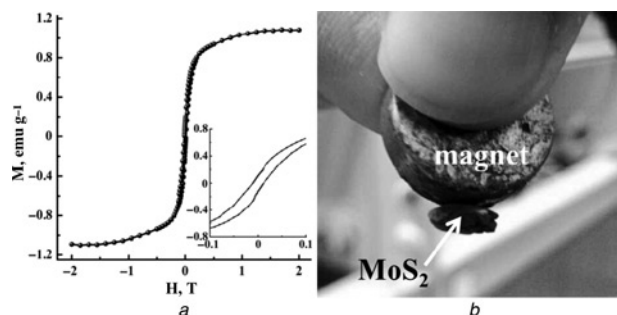


Figure 3 M–H hysteresis loops for MoS₂ nanowires measured at room temperature (Fig. 3a), inset is magnification of one segment; real picture showing that the MoS₂ nanowires powder are strongly attracted by permanent magnet (Fig. 3b)

The ferromagnetism observed in MoS₂ thin film and MoS₂ bulk at room temperature was attributed to the existence of the zigzag edges in the ferromagnetic ground state [29, 30]. The saturation magnetisation of MoS₂ thin film is 2.1 emu/g [29]. Here, the substantial ferromagnetism of the MoS₂ nanowires should originate from the presence of zigzag Mo-edges and sulphur vacancies because the MoS₂ nanowires are not completely sulphided because of the S/Mo atomic ratios 1.89.

4. Conclusion: In summary, single-crystalline MoS₂ nanowires were prepared by a hydrothermal method. HRTEM and SAED analysis show the nanowires present single-crystalline structures. The characterisation results of hysteresis loops (M–H) indicate that the single-crystalline nanowires present a substantial ferromagnetism at room temperatures. The substantial ferromagnetism of the MoS₂ nanowires should originate from the presence of zigzag Mo-edges and sulphur vacancies.

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6 References

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